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10EC56

**Fifth Semester B.E. Degree Examination, Dec.2017/Jan.2018**  
**Fundamentals of CMOS VLSI**

Time: 3 hrs.

Max. Marks:100

Note: 1. Answer any FIVE full questions, selecting at least TWO questions from each part.  
 2. Draw Neat diagram.

**PART - A**

- 1 a. Describe with neat diagrams, the P-well fabrication process. (08 Marks)  
 b. Explain the DC transfer characteristics of CMOS inverter and mark all the regions of operation with necessary expressions for  $V_{out}$  in each region. (08 Marks)  
 c. Compare CMOS and Bipolar Technology. (04 Marks)
- 2 a. Explain Transmission gate and Tristate inverter operations with neat diagram. (06 Marks)  
 b. Give the  $\lambda$ -based design rules for different layers, p and n MOSFETS and contact cuts. (08 Marks)  
 c. Obtain the stick diagram and layout of two way selector with enable. (06 Marks)
- 3 a. What are the features of CMOS Domino logic? Explain with neat diagram. (06 Marks)  
 b. In the following circuit find  $V_1, V_2, V_3$  and  $V_4$ . (06 Marks)

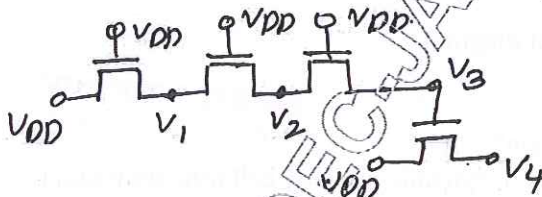


Fig Q3(b) 1

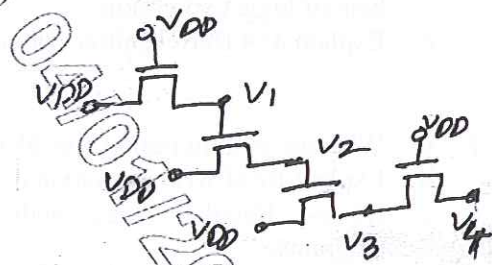


Fig Q3(b) 2

- c. Explain following logic structure with their salient features with neat diagram
  - i) Pseudo nMOS logic
  - ii) C<sup>2</sup>MOS logic
 (08 Marks)
- 4 a. Define sheet Resistance and standard unit of capacitance  $\square Cg$ . (06 Marks)  
 b. Explain cascaded inverter to drive large capacitance loads? Obtain an equation to find the number of stages. (08 Marks)  
 c. Calculate the total capacitance in terms of  $\square Cg$  for the following Fig.Q4(c) (06 Marks)

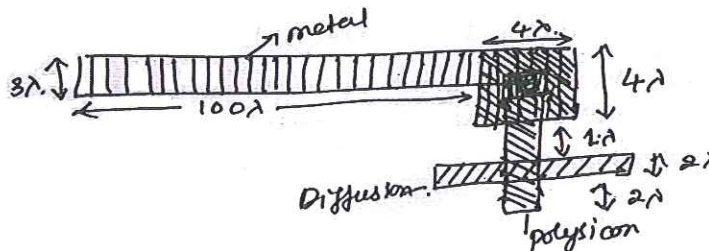


Fig Q4(c)

1 of 2

Important Note : 1. On completing your answers, compulsorily draw diagonal cross lines on the remaining blank pages.  
 2. Any revealing of identification, appeal to evaluator and /or equations written eg, 42+8 = 50, will be treated as malpractice.

**PART - B**

- 5 a. What are the properties of nMOS and PMOS switches? How TG is useful. (06 Marks)  
b. Explain the structure design of a parity generation with necessary diagrams and also write stick diagrams. (08 Marks)  
c. Obtain the logic implementation of 4-way multiplexer (Selector) using nMOS switches with necessary diagrams. (06 Marks)
- 6 a. Explain nMOS and CMOS non-inverting dynamic storage cell and draw the 4-bit shift register using nMOS. (07 Marks)  
b. How to implement arithmetic and logic operation with a standard adder? Explain with the help of logic expression. (06 Marks)  
c. Explain 4×4 Barrel shifter with neat diagram. (07 Marks)
- 7 a. What are system timing consideration? (05 Marks)  
b. Explain Read/write operation of one T dynamic memory cell (one transistor). (05 Marks)  
c. Discuss Baugh Worley method used for Two's complement multiplication with neat diagrams. (10 Marks)
- 8 a. Write a note on Testability and Testing. (06 Marks)  
b. What are different types of I/O pads? (06 Marks)  
c. Write short notes on:  
i) Built in self Test (BIST)  
ii) Scan design Technic. (08 Marks)

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